

# PolarHV™

## Power MOSFET

(Electrically Isolated Tab)

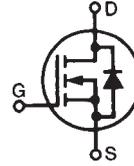
### IXTP 8N50PM

$$V_{DSS} = 500 \text{ V}$$

$$I_{D25} = 4 \text{ A}$$

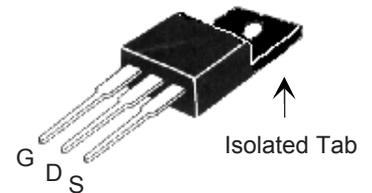
$$R_{DS(on)} \leq 0.8 \text{ } \Omega$$

N-Channel Enhancement Mode  
Avalanche Rated



Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	500	V
$V_{DGR}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GS} = 1 \text{ M}\Omega$	500	V
$V_{GS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	4	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	14	A
$I_{AR}$	$T_C = 25^\circ\text{C}$	8	A
$E_{AR}$	$T_C = 25^\circ\text{C}$	20	mJ
$E_{AS}$	$T_C = 25^\circ\text{C}$	400	mJ
$dv/dt$	$I_S \leq I_{DM}$ , $di/dt \leq 100 \text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ , $R_G = 18 \text{ } \Omega$	10	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	41	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
$T_{SOLD}$	Plastic body for 10 s	260	$^\circ\text{C}$
$M_d$	Mounting torque	1.13/10	Nm/lb.in.
<b>Weight</b>		4	g

OVERMOLDED TO-220  
(IXTP...M) OUTLINE



G = Gate      D = Drain  
S = Source

#### Features

- † Plastic overmolded tab for electrical isolation
- † International standard package
- † Unclamped Inductive Switching (UIS) rated
- † Low package inductance
- easy to drive and to protect

#### Advantages

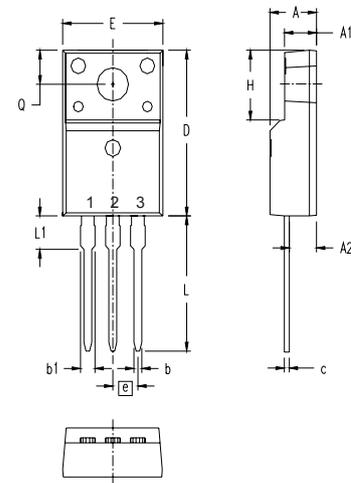
- † Easy to mount
- † Space savings
- † High power density

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 250 \text{ } \mu\text{A}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \text{ } \mu\text{A}$	3.0		5.5 V
$I_{GSS}$	$V_{GS} = \pm 30 \text{ V}_{DC}$ , $V_{DS} = 0$			$\pm 100 \text{ nA}$
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0 \text{ V}$			5 $\mu\text{A}$ 50 $\mu\text{A}$ $T_J = 125^\circ\text{C}$
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$ , $I_D = 4 \text{ A}$ Pulse test, $t \leq 300 \text{ } \mu\text{s}$ , duty cycle $d \leq 2 \%$			0.8 $\Omega$

Symbol	Test Conditions	Characteristic Values		
		(T <sub>J</sub> = 25° C, unless otherwise specified)		
		Min.	Typ.	Max.
<b>g<sub>fs</sub></b>	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 4 A	5	8	S
<b>C<sub>iss</sub></b>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1 MHz		1050	pF
<b>C<sub>oss</sub></b>			120	pF
<b>C<sub>rss</sub></b>			12	pF
<b>t<sub>d(on)</sub></b>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 0.5 V <sub>DSS</sub> , I <sub>D</sub> = 8 A R <sub>G</sub> = 18 Ω (External)		22	ns
<b>t<sub>r</sub></b>			28	ns
<b>t<sub>d(off)</sub></b>			65	ns
<b>t<sub>f</sub></b>			23	ns
<b>Q<sub>g(on)</sub></b>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 0.5 V <sub>DSS</sub> , I <sub>D</sub> = 4 A		20	nC
<b>Q<sub>gs</sub></b>			7	nC
<b>Q<sub>gd</sub></b>			7	nC
<b>R<sub>thJS</sub></b>				3.0 °C/W

**Source-Drain Diode**

Symbol	Test Conditions	Characteristic Values		
		(T <sub>J</sub> = 25° C, unless otherwise specified)		
		Min.	Typ.	Max.
<b>I<sub>S</sub></b>	V <sub>GS</sub> = 0 V			8 A
<b>I<sub>SM</sub></b>	Repetitive			14 A
<b>V<sub>SD</sub></b>	I <sub>F</sub> = I <sub>S</sub> , V <sub>GS</sub> = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			1.5 V
<b>t<sub>rr</sub></b>	I <sub>F</sub> = 3 A, V <sub>GS</sub> = 0 V, V <sub>R</sub> = 100 V -di/dt = 100 A/μs		400	ns

**ISOLATED TO-220 (IXTP...M)**


Terminals: 1 - Gate  
2 - Drain (Collector)  
3 - Source (Emitter)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.177	.193	4.50	4.90
A1	.092	.108	2.34	2.74
A2	.101	.117	2.56	2.96
b	.028	.035	0.70	0.90
b1	.050	.058	1.27	1.47
c	.018	.024	0.45	0.60
D	.617	.633	15.67	16.07
E	.392	.408	9.96	10.36
e	.100 BSC		2.54 BSC	
H	.255	.271	6.48	6.88
L	.499	.523	12.68	13.28
L1	.119	.135	3.03	3.43
∅P	.121	.129	3.08	3.28
Q	.126	.134	3.20	3.40

**PRELIMINARY TECHNICAL INFORMATION**

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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IXYS MOSFETs and IGBTs are covered by	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585
one or more of the following U.S. patents:	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405B2	6,759,692
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2